



# Correction: A 9T high-stable and Low-Energy Half-Select-Free SRAM Cell Design using TMDFETs

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The original article has been corrected.

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In this article, the authors affiliations were mismatched incorrectly, the affiliations have now been matched correctly.

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The original article can be found online at <https://doi.org/10.1007/s10470-022-02015-0>.

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